NE/SA572

DESCRIPTION

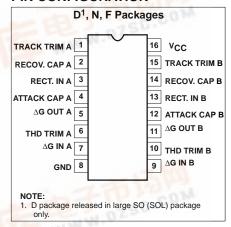
The NE572 is a dual-channel, high-performance gain control circuit in which either channel may be used for dynamic range compression or expansion. Each channel has a full-wave rectifier to detect the average value of input signal, a linearized, temperature-compensated variable gain cell (ΔG) and a dynamic time constant buffer. The buffer permits independent control of dynamic attack and recovery time with minimum external components and improved low frequency gain control ripple distortion over previous compandors.

The NE572 is intended for noise reduction in high-performance audio systems. It can also be used in a wide range of communication systems and video recording applications.

FEATURES

- Independent control of attack and recovery
- Improved low frequency gain control ripple
- Complementary gain compression and expansion with external op amp
- Wide dynamic range—greater than 110dB
- Temperature-compensated gain control
- Low distortion gain cell
- Low noise—6μV typical
- Wide supply voltage range—6V-22V
- System level adjustable with external components

PIN CONFIGURATION



APPLICATIONS

- Dynamic noise reduction system
- Voltage control amplifier
- Stereo expandor
- Automatic level control
- High-level limiter
- Low-level noise gate
- State variable filter

ORDERING INFORMATION

DESCRIPTION	TEMPERATURE RANGE	ORDER CODE	DWG#	
16-Pin Plastic Small Outline (SO)	0 to +70°C	NE572D	0005	
16-Pin Plastic Dual In-Line Package (DIP)	0 to +70°C	NE572N	0406	
16-Pin Plastic Small Outline (SO)	−40 to +85°C	SA572D	0005	
16-Pin Ceramic Dual In-Line Package (Cerdip)	−40 to +85°C	SA572F	0582	
16-Pin Plastic Dual In-Line Package (DIP)	−40 to +85°C	SA572N	0406	

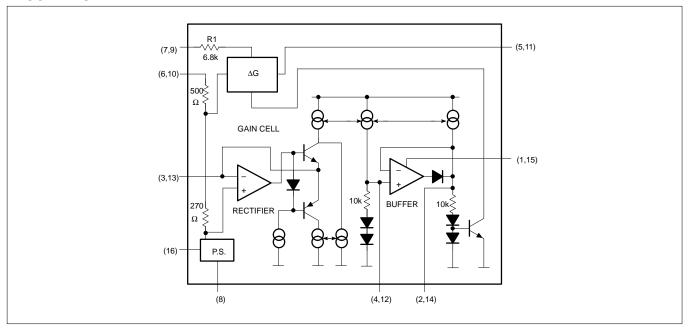
ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	TER RATING	
V _{CC}	Supply voltage	22	V_{DC}
T _A	Operating temperature range		
1	NE572	0 to +70	°C
400 7	SA572	-40 to +85	
P _D	Power dissipation	500	mW



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BLOCK DIAGRAM



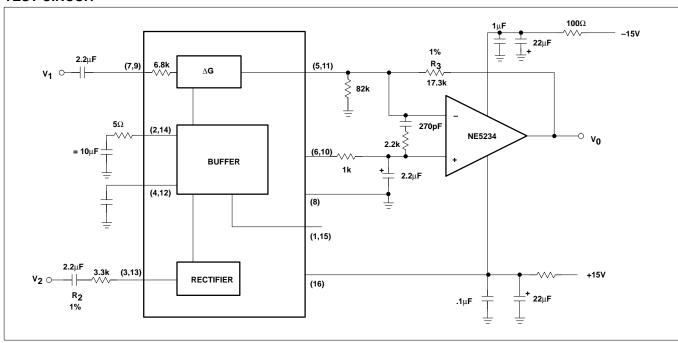
DC ELECTRICAL CHARACTERISTICS

Standard test conditions (unless otherwise noted) V_{CC} =15V, T_A =25°C; Expandor mode (see Test Circuit). Input signals at unity gain level (0dB) = 100m V_{RMS} at 1kHz; V_1 = V_2 ; R_2 = 3.3k Ω ; R_3 = 17.3k Ω .

SYMBOL	PARAMETER	TEST CONDITIONS	NE572			SA572			UNIT
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	Supply voltage		6		22	6		22	V_{DC}
I _{CC}	Supply current	No signal			6			6.3	mA
V _R	Internal voltage reference		2.3	2.5	2.7	2.3	2.5	2.7	V_{DC}
THD	Total harmonic distortion (untrimmed)	1kHz C _A =1.0μF		0.2	1.0		0.2	1.0	%
THD	Total harmonic distortion (trimmed)	1kHz C _R =10μF		0.05			0.05		%
THD	Total harmonic distortion (trimmed)	100Hz		0.25			0.25		%
	No signal output noise	Input to V ₁ and V ₂ grounded (20–20kHz)		6	25		6	25	μV
	DC level shift (untrimmed)	Input change from no signal to 100mV _{RMS}		±20	±50		±20	±50	mV
	Unity gain level		-1	0	+1	-1.5	0	+1.5	dB
	Large-signal distortion	V ₁ =V ₂ =400mV		0.7	3.0		0.7	3	%
	Tracking error (measured								
	relative to value at unity	Rectifier input							
	gain)=	V ₂ =+6dB V ₁ =0dB		±0.2			±0.2		
	[V _O -V _O (unity gain)]dB	V_2 =-30dB V_1 =0dB		±0.5	-1.5		±0.5	-2.5	dB
	-V ₂ dB				+0.8			+1.6	
	Channel crosstalk	200mV _{RMS} into channel A, measured output on channel B	60			60			dB
PSRR	Power supply rejection ratio	120Hz		70			70		dB

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TEST CIRCUIT



AUDIO SIGNAL PROCESSING IC COMBINES VCA AND FAST AT-TACK/SLOW RECOVERY LEVEL SENSOR

In high-performance audio gain control applications, it is desirable to independently control the attack and recovery time of the gain control signal. This is true, for example, in compandor applications for noise reduction. In high end systems the input signal is usually split into two or more frequency bands to optimize the dynamic behavior for each band. This reduces low frequency distortion due to control signal ripple, phase distortion, high frequency channel overload and noise modulation. Because of the expense in hardware, multiple band signal processing up to now was limited to professional audio applications.

With the introduction of the Signetics NE572 this high-performance noise reduction concept becomes feasible for consumer hi fi applications. The NE572 is a dual channel gain control IC. Each channel has a linearized, temperature-compensated gain cell and an improved level sensor. In conjunction with an external low noise op amp for current-to-voltage conversion, the VCA features low distortion, low noise and wide dynamic range.

The novel level sensor which provides gain control current for the VCA gives lower gain control ripple and independent control of fast attack, slow recovery dynamic response. An

attack capacitor C_A with an internal 10k resistor R_A defines the attack time t_A . The recovery time t_R of a tone burst is defined by a recovery capacitor C_R and an internal 10k resistor R_R . Typical attack time of 4ms for the high-frequency spectrum and 40ms for the low frequency band can be obtained with $0.1\mu F$ and $1.0\mu F$ attack capacitors, respectively. Recovery time of 200ms can be obtained with a $4.7\mu F$ recovery capacitor for a 100Hz signal, the third harmonic distortion is improved by more than 10dB over the simple RC ripple filter with a single $1.0\mu F$ attack and recovery capacitor, while the attack time remains the same.

The NE572 is assembled in a standard 16-pin dual in-line plastic package and in oversized SOL package. It operates over a wide supply range from 6V to 22V. Supply current is less than 6mA. The NE572 is designed for consumer application over a temperature range 0-70 The SA572 is intended for applications from –40°C to +85°C.

NE572 BASIC APPLICATIONS

Description

The NE572 consists of two linearized, temperature-compensated gain cells (ΔG), each with a full-wave rectifier and a buffer amplifier as shown in the block diagram. The two channels share a 2.5V common bias reference derived from the power supply but otherwise operate independently. Because of

inherent low distortion, low noise and the capability to linearize large signals, a wide dynamic range can be obtained. The buffer amplifiers are provided to permit control of attack time and recovery time independent of each other. Partitioned as shown in the block diagram, the IC allows flexibility in the design of system levels that optimize DC shift, ripple distortion, tracking accuracy and noise floor for a wide range of application requirements.

Gain Cell

Figure 1 shows the circuit configuration of the gain cell. Bases of the differential pairs $\mathrm{Q}_1\text{-}\mathrm{Q}_2$ and $\mathrm{Q}_3\text{-}\mathrm{Q}_4$ are both tied to the output and inputs of OPA A₁. The negative feedback through Q₁ holds the V_{BE} of Q₁-Q₂ and the V_{BE} of Q₃-Q₄ equal. The following relationship can be derived from the transistor model equation in the forward active region.

$$\Delta V_{BE}_{Q3Q4} = \Delta_{BE}_{Q1Q2}$$

$$(V_{BE} = V_T I_{IN} IC/IS)$$

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$$V_{T}I_{n} = \frac{\frac{1}{2}I_{G} - \frac{1}{2}I_{O}}{I_{S}} \qquad V_{T}I_{n} = \frac{\frac{1}{2}I_{G} - \frac{1}{2}I_{O}}{I_{S}}$$

where
$$I_{IN}=\frac{V_{IN}}{R_1}$$

$$R_1=6.8k\Omega$$

$$I_1=140\mu A$$

$$I_1 = 140 \mu A$$

 $I_2 = 280 \mu A$

$$V_T I_n = \frac{I_1 - I_{IN}}{I_S}$$
 $V_T I_n = \frac{I_2 - I_1 - I_{IN}}{I_S}$ (2)

where
$$I_{IN}=\frac{V_{IN}}{R_1}$$

$$R_1=6.8k\Omega$$

$$I_1=140\mu A$$

$$I_2=280\mu A$$

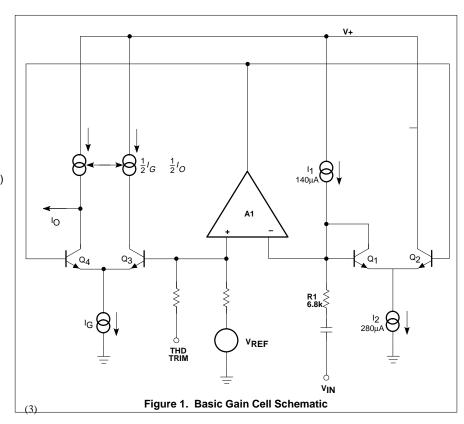
IO is the differential output current of the gain cell and IG is the gain control current of the gain cell.

If all transistors Q1 through Q4 are of the same size, equation (2) can be simplified to:

$$I_O \; = \; \frac{2}{I_2} \quad \; I_{IN} \quad \; I_G \quad \; \frac{1}{I_2} \; I_2 \quad \; 2I_1 \quad \; I_G \label{eq:IO}$$

The first term of Equation 3 shows the multiplier relationship of a linearized two quadrant transconductance amplifier. The second term is the gain control feedthrough due to the mismatch of devices. In the design, this has been minimized by large matched devices and careful layout. Offset voltage is caused by the device mismatch and it leads to even harmonic distortion. The offset voltage can be trimmed out by feeding a current source within ±25µA into the THD trim pin.

The residual distortion is third harmonic distortion and is caused by gain control ripple. In a compandor system, available control of fast attack and slow recovery improve ripple distortion significantly. At the unity gain level of 100mV, the gain cell gives THD (total harmonic distortion) of 0.17% typ. Output noise with no input signals is only 6uV in the audio spectrum (10Hz-20kHz). The output current IO must feed the virtual ground input of an operational amplifier with a resistor from output to inverting input. The non-inverting input of the operational amplifier has to be biased at VREF if the output current IO is DC coupled.



Rectifier

The rectifier is a full-wave design as shown in Figure 2. The input voltage is converted to current through the input resistor R2 and turns on either Q5 or Q6 depending on the signal polarity. Deadband of the voltage to current converter is reduced by the loop gain of the gain block A2. If AC coupling is used, the rectifier error comes only from input bias current of gain block A2. The input bias current is typically about 70nA. Frequency response of the gain block A2 also causes second-order error at high frequency. The collector current of Q₆ is mirrored and summed at the collector of Q5 to form the full wave rectified output current IR. The rectifier transfer function is

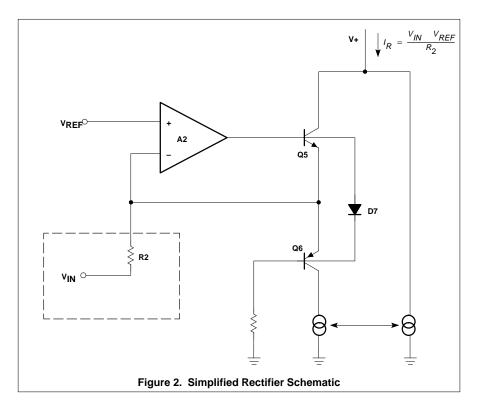
$$I_R = \frac{V_{IN} \quad V_{REF}}{R_2} \tag{4}$$

If $V_{\mbox{\scriptsize IN}}$ is AC-coupled, then the equation will be

$$I_{RAC} = \frac{V_{IN}(AVG)}{R_2}$$

The internal bias scheme limits the maximum output current IR to be around 300µA. Within a ±1dB error band the input range of the rectifier is about 52dB.

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Q8 Q9 Q10 I_Q = 2I_{R2} X2 Q16 I_R = V_{IN} I_Q = 2I_{R2} X2 Q16 I_R = V_{IN} I

Buffer Amplifier

In audio systems, it is desirable to have fast attack time and slow recovery time for a tone burst input. The fast attack time reduces transient channel overload but also causes low-frequency ripple distortion. The low-frequency ripple distortion can be improved with the slow recovery time. If different attack times are implemented in corresponding frequency spectrums in a split band audio system, high quality performance can be achieved. The buffer amplifier is designed to make this feature available with minimum external components. Referring to Figure 3, the rectifier output current is mirrored into the input and output of the unipolar buffer amplifier A₃ through Q₈, Q₉ and Q₁₀. Diodes D₁₁ and D₁₂ improve tracking accuracy and provide common-mode bias for A3. For a positive-going input signal, the buffer amplifier acts like a voltage-follower. Therefore, the output impedance of A₃ makes the contribution of capacitor CR to attack time insignificant. Neglecting diode impedance, the gain Ga(t) for ΔG can be expressed as follows:

$$Ga(t) = (Ga_{INT} \quad Ga_{FNL} e^{-\frac{t}{A}} \quad Ga_{FNL}$$

Ga_{INT}=Initial Gain

GaFNL=Final Gain

$$\tau_A=R_A \bullet CA=10k \bullet CA$$

where τ_A is the attack time constant and R_A is a 10k internal resistor. Diode D_{15} opens the feedback loop of A_3 for a negative-going signal if the value of capacitor CR is larger than capacitor CA. The recovery time depends only on CR \bullet $R_R.$ If the diode impedance is assumed negligible, the dynamic gain G_R (t) for ΔG is expressed as follows.

$$G_R(t) = (G_{RINT} \quad G_{RFNL} e^{-\frac{t}{R}} \quad G_{RFNL}$$

$$G_R(t)=(G_{R \text{ INT}}-G_{R \text{ FNL}}) e +G_{R \text{ FNL}}$$

$$\tau R=R_R \bullet CR=10k \bullet CR$$

where τR is the recovery time constant and R_R is a 10k internal resistor. The gain control current is mirrored to the gain cell through Q_{14} . The low level gain errors due to input bias current of A_2 and A_3 can be trimmed through the tracking trim pin into A_3 with a current source of $\pm 3\mu A$.

Basic Expandor

Figure 4 shows an application of the circuit as a simple expandor. The gain expression of the system is given by

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$$\frac{V_{OUT}}{V_{IN}} = \frac{2}{I_1} \frac{R_3 V_{IN(AVG)}}{R_2 R_1}$$
(5)
(I₁=140 μ A)

Both the resistors R_1 and R_2 are tied to internal summing nodes. R_1 is a 6.8k internal resistor. The maximum input current into the gain cell can be as large as $140\mu A$. This corresponds to a voltage level of $140\mu A$ • 6.8k=952mV peak. The input peak current into the rectifier is limited to $300\mu A$ by the internal bias system. Note that the value of R_1 can be increased to accommodate higher input level. R_2 and R_3 are external resistors. It is easy to adjust the ratio of R_3/R_2 for

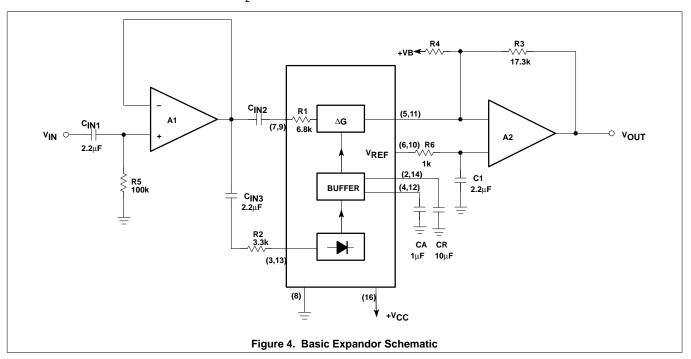
desirable system voltage and current levels. A small R_2 results in higher gain control current and smaller static and dynamic tracking error. However, an impedance buffer A_1 may be necessary if the input is voltage drive with large source impedance.

The gain cell output current feeds the summing node of the external OPA A_2 . R_3 and A_2 convert the gain cell output current to the output voltage. In high-performance applications, A_2 has to be low-noise, high-speed and wide band so that the high-performance output of the gain cell will not be degraded. The non-inverting input of A_2 can be biased at the low noise internal

reference Pin 6 or 10. Resistor R_4 is used to bias up the output DC level of A_2 for maximum swing. The output DC level of A_2 is given by

$$V_{ODC} = V_{REF} \ 1 \quad \frac{R_3}{R_4} \quad V_B \frac{R_3}{R_4}$$
 (6)

 V_{B} can be tied to a regulated power supply for a dual supply system and be grounded for a single supply system. CA sets the attack time constant and CR sets the recovery time constant. *5COL $\,$



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Basic Compressor

Figure 5 shows the hook-up of the circuit as a compressor. The IC is put in the feedback loop of the OPA A_1 . The system gain expression is as follows:

$$\frac{V_{OUT}}{V_{IN}} = \frac{I_1}{2} \frac{R_2 R_1}{R_3 V_{IN(AVG)}}^{\frac{1}{2}}$$
 (7)

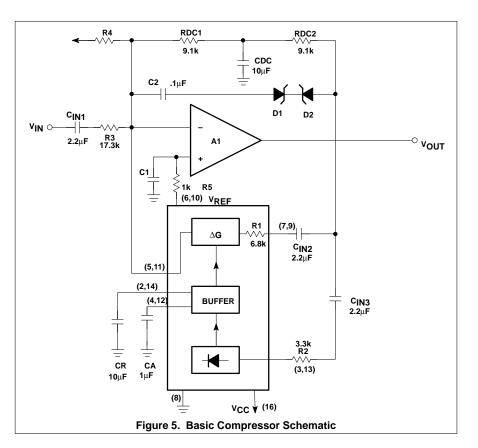
 $R_{DC1},\,R_{DC2},\,$ and CDC form a DC feedback for A₁. The output DC level of A₁ is given by

$$V_{ODC} = V_{REF} \quad 1 \quad \frac{R_{DC1} \quad R_{DC2}}{R_4}$$
 (8)
$$V_{B} \quad \frac{R_{DC1} \quad R_{DC2}}{R_4}$$

The zener diodes D_1 and D_2 are used for channel overload protection.

Basic Compandor System

The above basic compressor and expandor can be applied to systems such as tape/disc noise reduction, digital audio, bucket brigade delay lines. Additional system design techniques such as bandlimiting, band splitting, pre-emphasis, de-emphasis and equalization are easy to incorporate. The IC is a versatile functional block to achieve a high performance audio system. Figure 6 shows the system level diagram for reference.



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